

# Zhizhong Yuan

## List of Publications by Year in descending order

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13  
papers

551  
citations

933447

10  
h-index

1125743

13  
g-index

15  
all docs

15  
docs citations

15  
times ranked

715  
citing authors

#	ARTICLE	IF	CITATIONS
1	Deformation microstructures of austenitic stainless steel 2Cr13Mn9Ni4 under ultrafast strain rate by laser shock processing. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2013, 587, 244-249.	5.6	11
2	Silicon Nanocrystals as an Enabling Material for Silicon Photonics. <i>Proceedings of the IEEE</i> , 2009, 97, 1250-1268.	21.3	74
3	High-cycle fatigue behavior of high-nitrogen austenitic stainless steel. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2009, 517, 257-260.	5.6	25
4	Enhanced photoluminescence of Tb <sup>3+</sup> in SnO <sub>2</sub> film by phosphorus diffusion process. <i>Journal of Alloys and Compounds</i> , 2009, 474, 246-249.	5.5	11
5	Electron-beam-induced current evidence for room-temperature photoluminescence of silicon pn diode. <i>Vacuum</i> , 2008, 82, 1337-1340.	3.5	3
6	Photoluminescence of Tb <sup>3+</sup> -doped SiN <sub>x</sub> films with different Si concentrations. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 146, 126-130.	3.5	6
7	Impact properties of high-nitrogen austenitic stainless steels. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2008, 475, 202-206.	5.6	24
8	Enhancement of ZnO light emission via coupling with localized surface plasmon of Ag island film. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	156
9	Electroluminescence of SnO <sub>2</sub> -p-Si heterojunction. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	55
10	Correlation between luminescence and structural evolution of Si-rich silicon oxide film annealed at different temperatures. <i>Journal of Applied Physics</i> , 2007, 101, 103504.	2.5	29
11	Photoluminescence of Si-rich silicon nitride: Defect-related states and silicon nanoclusters. <i>Applied Physics Letters</i> , 2007, 90, 131903.	3.3	124
12	Effects of defect, carrier concentration and annealing process on the photoluminescence of silicon pn diodes. <i>Materials Science in Semiconductor Processing</i> , 2007, 10, 173-178.	4.0	4
13	Photoluminescence of Tb <sup>3+</sup> doped SiN <sub>x</sub> films grown by plasma-enhanced chemical vapor deposition. <i>Journal of Applied Physics</i> , 2006, 100, 083106.	2.5	25